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STMicroelectronics T610T-8T

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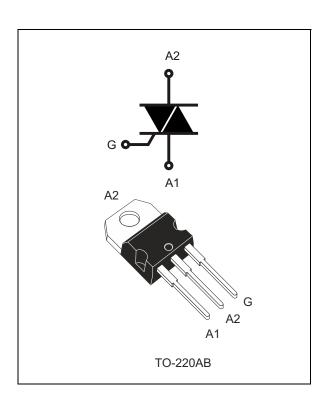




# T610T-8T

# 6 A logic level Triac

Datasheet - production data



## **Description**

Available in through-hole package, the T610T-8T Triac can be used for the on/off or phase angle control function in general purpose AC switching. This device can be directly driven by a microcontroller due to its 10 mA gate current requirement.

Table 1. Device summary

| Symbol                              | Value | Unit |
|-------------------------------------|-------|------|
| I <sub>T(rms)</sub>                 | 6     | А    |
| $V_{DRM}, V_{RRM}$                  | 800   | V    |
| V <sub>DSM</sub> , V <sub>RSM</sub> | 900   | V    |
| I <sub>GT</sub>                     | 10    | mA   |

### **Features**

- Medium current Triac
- · Three quadrants
- ECOPACK®2 compliant component

# **Applications**

- · General purpose AC line load switching
- Motor control circuits
- · Small home appliances
- Lighting
- · Inrush current limiting circuits
- Overvoltage crowbar protection



Characteristics T610T-8T

## 1 Characteristics

Table 2. Absolute ratings (limiting values,  $T_j = 25$  °C unless otherwise stated)

| Symbol                                 | Parameter  |                         |                         | Value         | Unit             |
|--|--|-------------------------|-------------------------|---------------|------------------|
| I <sub>T(rms)</sub>                    | On-state rms current (full sine wave)  |                         | T <sub>c</sub> = 135 °C | 6             | Α                |
| 1.                                     | Non repetitive surge peak on-state   | f = 50 Hz               | t = 20 ms               | 45            | Α                |
| I <sub>TSM</sub>                       | current (full cycle, T <sub>j</sub> initial = 25 °C)   | f = 60 Hz               | t = 16.7 ms             | 47            | ^                |
| l <sup>2</sup> t                       | I <sup>2</sup> t value for fusing, T <sub>j</sub> initial = 25 °C                            |                         | t <sub>p</sub> = 10 ms  | 13            | A <sup>2</sup> s |
| V <sub>DRM</sub> ,                     | Repetitive surge peak off-state volta  | T <sub>j</sub> = 150 °C | 600                     | V             |                  |
| $V_{RRM}$                              | Repetitive surge peak oil-state voita  | T <sub>j</sub> = 125 °C | 800                     | V             |                  |
| V <sub>DSM</sub> ,<br>V <sub>RSM</sub> | Non repetitive surge peak off-state v  | t <sub>p</sub> = 10 ms  | 900                     | V             |                  |
| dl/dt                                  | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \le 100 \text{ ns}$ |                         | F = 100 Hz              | 100           | A/μs             |
| I <sub>GM</sub>                        | Peak gate current $t_p = 20 \mu s$   |                         | T <sub>j</sub> = 150 °C | 4             | Α                |
| P <sub>G(AV)</sub>                     | Average gate power dissipation $T_j = 150^{\circ}$ C   |                         |                         | 1             | W                |
| T <sub>stg</sub>                       | Storage junction temperature range   |                         |                         | - 40 to + 150 | °C               |
| Tj                                     | Operating junction temperature range   |                         |                         | - 40 to + 150 | <u> </u>         |
| $T_L$                                  | Maximum lead temperature for soldering during 10 s   |                         |                         | 260           | °C               |

Table 3. Electrical characteristics ( $T_j = 25$  °C, unless otherwise specified)

| Symbol                        | Test conditions  | Quadrant                |         | Value | Unit   |
|-------------------------------|--|-------------------------|---------|-------|--------|
|                               | $V_D = 12 \text{ V}, R_L = 30 \Omega$                            | 1 11 111                | Min.    | 0.5   | A      |
| I <sub>GT</sub>               |  | 1 - 11 - 111            | Max.    | 10    | - mA   |
| V <sub>GT</sub>               | $V_D = 12 \text{ V}, R_L = 30 \Omega$                            | 1 - 11 - 111            | Max.    | 1.3   | V      |
| $V_{\sf GD}$                  | $V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 150 \text{ °C}$ | 1 - 11 - 111            | Min.    | 0.2   | V      |
| I <sub>H</sub> <sup>(1)</sup> | I <sub>T</sub> = 500 mA  |                         | Max.    | 15    | mA     |
|                               | I <sub>G</sub> = 1.2 I <sub>GT</sub>                             | 1 - 111                 | Max.    | 20    | mA     |
| ۱L                            |  | II                      |         | 25    |        |
| dV/dt <sup>(1)</sup>          | $V_D = V_R = 536 \text{ V, gate open}$                           | T <sub>j</sub> = 125 °C | N 4:    | 250   | V/µs   |
| uv/ut\ /                      | $V_D = V_R = 402 \text{ V, gate open}$                           | T <sub>j</sub> = 150 °C | Min.    | 170   | V/µs   |
| (dl/dt)c <sup>(1)</sup>       | (dV/dt)c = 0.1 V/μs  | T <sub>j</sub> = 125 °C | Min.    | 5.2   | A/ms   |
| (ai/at)c(1)                   |  | T <sub>j</sub> = 150 °C |         | 3.7   |        |
| (dl/dt)c <sup>(1)</sup>       | (1) (1)  | T <sub>j</sub> = 125 °C | Min.    | 2.7   | A /ma  |
| (al/at)c···                   | $(dV/dt)c = 10 V/\mu s$  | T <sub>j</sub> = 150 °C | IVIIII. | 1.2   | - A/ms |

<sup>1.</sup> For both polarities of A2 referenced to A1

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**Table 4. Static characteristics** 

| Symbol                        | Test conditions                                  |                         | Value | Unit |      |
|-------------------------------|--|-------------------------|-------|------|------|
| V <sub>T</sub> <sup>(1)</sup> | I <sub>TM</sub> = 8.5 A, t <sub>p</sub> = 380 μs | T <sub>j</sub> = 25 °C  | Max.  | 1.55 | V    |
| V <sub>t0</sub> (1)           | Threshold voltage                                | T <sub>j</sub> = 150 °C | Max.  | 0.85 | V    |
| R <sub>d</sub> <sup>(1)</sup> | Dynamic resistance                               | T <sub>j</sub> = 150 °C | Max.  | 75   | mΩ   |
| I <sub>DRM</sub>              | V -V - 900 V                                     | T <sub>j</sub> = 25 °C  | Max.  | 5    | μΑ   |
|                               | $V_{DRM} = V_{RRM} = 800 \text{ V}$              | T <sub>j</sub> = 125 °C |       | 0.6  | A    |
| I <sub>RRM</sub>              | V <sub>DRM</sub> = V <sub>RRM</sub> = 600 V      | T <sub>j</sub> = 150 °C | Max.  | 2.0  | ⊢ mA |

<sup>1.</sup> For both polarities of A2 referenced to A1

Table 5. Thermal resistance

| Symbol               | Parameter                | Value | Unit |
|----------------------|--------------------------|-------|------|
| R <sub>th(j-c)</sub> | Junction to case (AC)    | 2.1   | °C/W |
| R <sub>th(j-a)</sub> | Junction to ambient (DC) | 60    | °C/W |

Figure 1. Maximum power dissipation versus on-state rms current

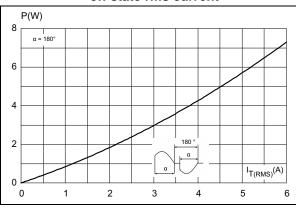


Figure 2. On-state rms current versus case temperature

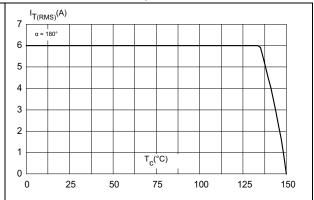


Figure 3. On-state rms current versus ambient temperature (free air convection)

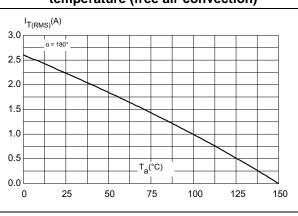
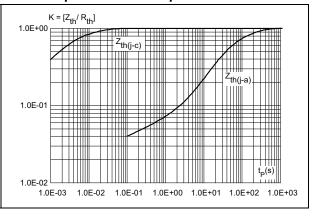


Figure 4. Relative variation of thermal impedance versus pulse duration







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Figure 5. On-state characteristics (maximum values)

 $I_{TM}(A)$ 100 T max: 0.85 V  $V_{to}^{\perp} = 0.85 \text{ V}$  $R_d = 75 \text{ m}\Omega$ 10 = 150 °C = 25 °C  $V_{TM}(V)$ 0.0 2.0 2.5 3.5 4.0 0.5 1.0 1.5 3.0

Figure 6. Surge peak on-state current versus number of cycles

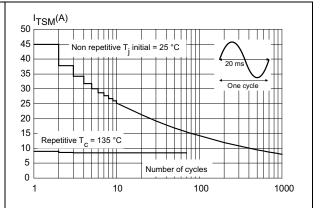
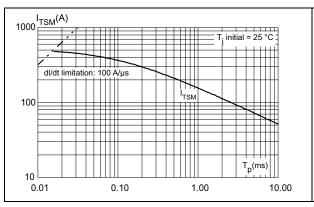


Figure 7. Non repetitive surge peak on-state current

Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)



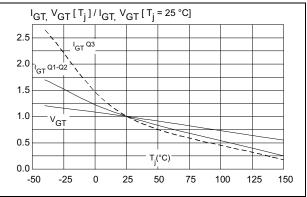
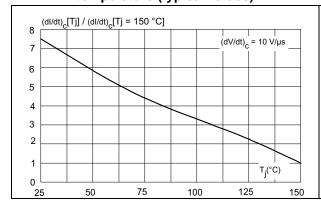
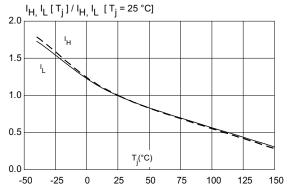


Figure 9. Relative variation of critical rate of decrease of main current versus junction temperature (typical values)

Figure 10. Relative variation of holding current and latching current versus junction temperature (typical values)





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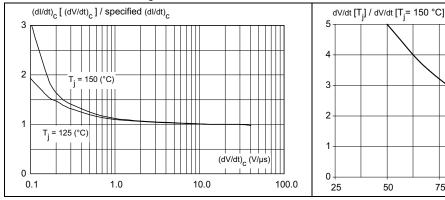


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Figure 11. Relative variation of critical rate of decrease of main current (dl/dt)<sub>C</sub> versus reapplied (dV/dt)<sub>C</sub> (maximum values)

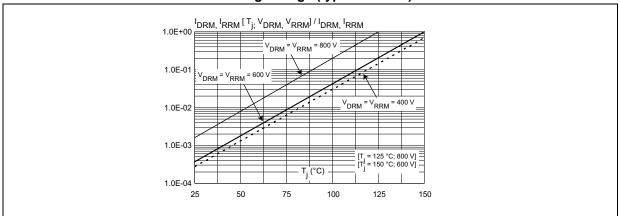
Figure 12. Relative variation of static dV/dt immunity versus junction temperature (typical values)

V<sub>D</sub> = V<sub>R</sub> = 402 V; 150 (°C)



2 1 1 0 25 50 75 100 125 150

Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)





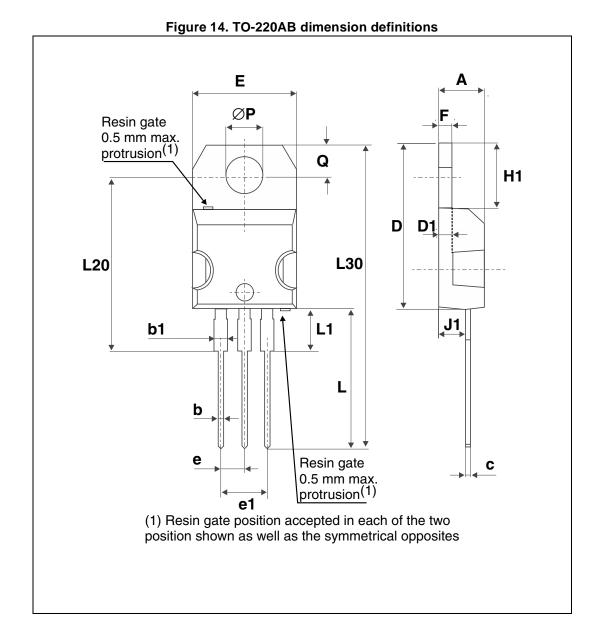
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Package information T610T-8T

## 2 Package information

- Epoxy meets UL94, V0
- Lead-free package
- Recommended torque: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.





T610T-8T Package information

### Table 6. TO-220AB dimension values

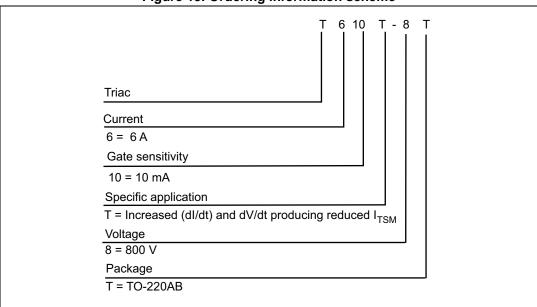
|      | Dimensions  |       |           |       |  |
|------|-------------|-------|-----------|-------|--|
| Ref. | Millimeters |       | Incl      | hes   |  |
|      | Min.        | Max.  | Min.      | Max.  |  |
| А    | 4.40        | 4.60  | 0.17      | 0.18  |  |
| b    | 0.61        | 0.88  | 0.024     | 0.035 |  |
| b1   | 1.14        | 1.70  | 0.045     | 0.067 |  |
| С    | 0.48        | 0.70  | 0.019     | 0.027 |  |
| D    | 15.25       | 15.75 | 0.60      | 0.62  |  |
| D1   | 1.27 typ.   |       | 0.05 typ. |       |  |
| E    | 10          | 10.40 | 0.39      | 0.41  |  |
| е    | 2.40        | 2.70  | 0.094     | 0.106 |  |
| e1   | 4.95        | 5.15  | 0.19      | 0.20  |  |
| F    | 1.23        | 1.32  | 0.048     | 0.052 |  |
| H1   | 6.20        | 6.60  | 0.24      | 0.26  |  |
| J1   | 2.40        | 2.72  | 0.094     | 0.107 |  |
| L    | 13          | 14    | 0.51      | 0.55  |  |
| L1   | 3.50        | 3.93  | 0.137     | 0.154 |  |
| L20  | 16.40 typ.  |       | 0.64 typ. |       |  |
| L30  | 28.90 typ.  |       | 1.13 typ. |       |  |
| ØP   | 3.75        | 3.85  | 0.147     | 0.151 |  |
| Q    | 2.65        | 2.95  | 0.104     | 0.116 |  |



Ordering information T610T-8T

# 3 Ordering information

Figure 15. Ordering information scheme



**Table 7. Ordering information** 

| Order code | Marking  | Package  | Weight | Base qty | Delivery mode |
|------------|----------|----------|--------|----------|---------------|
| T610T-8T   | T610T-8T | TO-220AB | 2.0 g  | 50       | Tube          |

# 4 Revision history

Table 8. Document revision history

| Date        | Revision | Changes          |
|-------------|----------|------------------|
| 07-Nov-2014 | 1        | Initial release. |

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### Distributor of STMicroelectronics: Excellent Integrated System Limited

Datasheet of T610T-8T - TRIAC 800V 6A 10MA TO-220AB

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#### T610T-8T

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